SOT023 ṂṂ Ł NPN ÆṀ ɥ s ǁ ˀ Silicon NPN transistor in a SOT-23 Plastic Package.

љ 8550M Ӣ ´ ı ṇ̀ ƒ ᵝ

Complementary pair with 8550M,HF Product.

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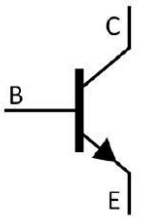
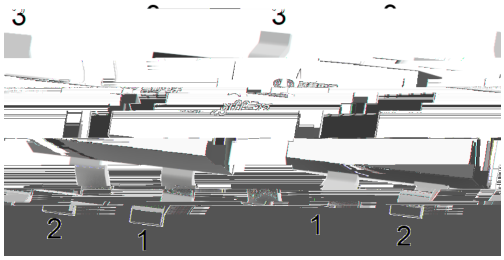
Power amplifier applications.





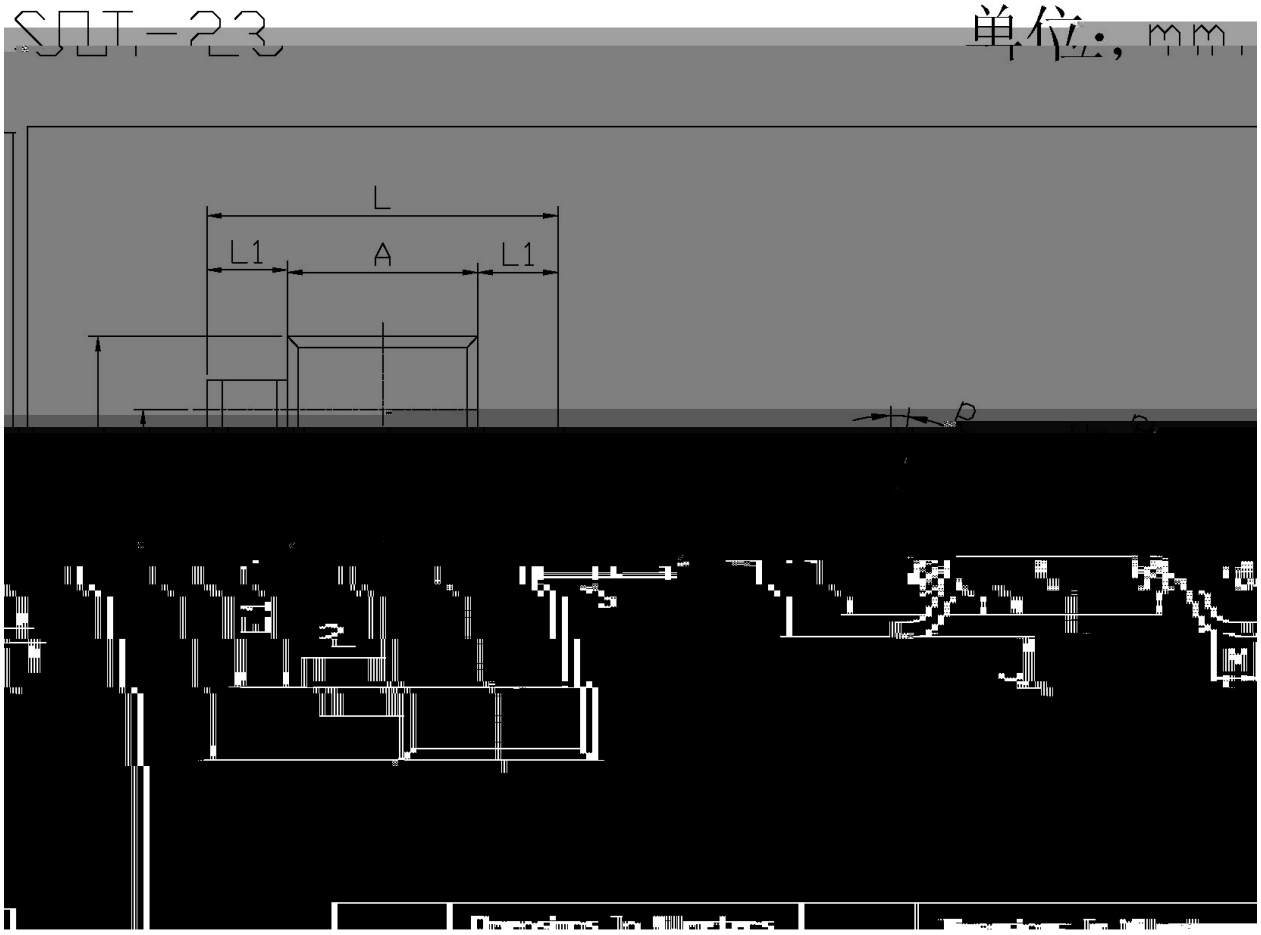
PIN1 χ Base PIN 2 χ Emitter PIN 3 χ Collector

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	85~160	120~200	160~300
Marking	HY1B	HY1C	HY1D

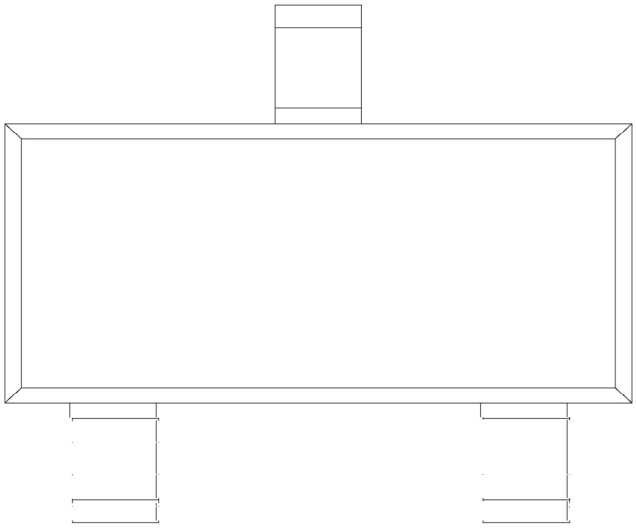
v ̈Ω̣ Parameter	ɬ Symbol	̈Ω̣Ö Rating	ɒ ɧ Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	1.5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	ɬ
Storage Temperature Range	T_{stg}	-55 Ḱ 150	ɬ

v ̈Ω̣ Parameter	ɬ Symbol	⊥⊥ ;ǀ ʈ Test Conditions	ω̣ ṇ Ö Min	ɛ ʒ Ö Typ	ω̣ ʑ Ö Max	ɒ ɧ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=2.0mA I_B=0	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_C=0.1mA I_C=0	C B O			

SOT-23 单位：mm







ب ˝ χ

H χ ⰼ ⰳ ⰵ

Y1 χ ⰼ ⰴ ⰵ

C χ ⰼ k_{FE} ˋ ⰻ

Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 أ ♬ □ ỷ 150 Ḱ 180 ɫ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ɫ ı `H ڑ ˈY ⺈ ⺾ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ھ ỷ ⺾ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:150~180 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɫ /sec.

□ ỷ χ 260 ° 5 ɫ `H ڑ χ 10 ° 1 sec.

Temp.:260 ° 5 ɫ Time:10 ° 1 sec

ɔ` γ ⊢ / REEL

Package Type	Units					Dimension (unit mm³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7		